

**Amendments to the Claims:**

The listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

Claims 1 – 10 (cancelled)

Claim 11 (currently amended)      A ~~kind of~~ non-volatile memory structure, including:  
a base;  
a gate dielectric layer on the base, the gate dielectric layer with an increased electron trapping density has at least one kind of hetero element, other than Nitrogen, ~~to increase the electron trapping density;~~  
a gate electrode layer on the top of the said gate dielectric layer; and  
a source/drain electrodes at the base on both sides of the said gate dielectric layer.

Claim 12 (previously presented)      The non-volatile memory structure as claimed in claim 11, where the gate dielectric layer in turns from bottom to the top including a first oxide layer, a nitride layer and a second oxide layer.

Claim 13 (previously presented)      The non-volatile memory structure as claimed in claim 11, where the hetero elements used are any one within Germanium (Ge), Silicon (Si), Oxygen (O<sub>2</sub>), Oxygen (O) separately or multiple mixture therefrom.

Claim 14 (previously presented)      The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Germanium (Ge), Silicon (Si), Oxygen (O).

Claim 15 (new)      The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Germanium (Ge).

Claim 16 (new)      The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Oxygen (O).